MJ21195G - PNP MJ21196G - NPN

Silicon Power Transistors

The MJ21195G and MJ21196G utilize Perforated Emitter technology and are specifically designed for high power audio output, disk head positioners and linear applications.

Features

- Total Harmonic Distortion Characterized
- High DC Current Gain
- Excellent Gain Linearity
- High SOA
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CBO}	400	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector-Emitter Voltage - 1.5V	V _{CEX}	400	Vdc
Collector Current - Continuous	I _C	16	Adc
Collector Current - Peak (Note 1)	I _{CM}	30	Adc
Base Current - Continuous	I _B	5	Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 μs, Duty Cycle ≤10%.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C/W

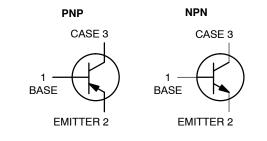


ON Semiconductor®

http://onsemi.com

16 AMPERES **COMPLEMENTARY SILICON-POWER TRANSISTORS 250 VOLTS, 250 WATTS**

SCHEMATIC





TO-204AA (TO-3) **CASE 1-07** STYLE 1

MARKING DIAGRAM

MJ2119xG **AYWW** MEX

MJ2119x = Device Code

x = 5 or 6

G = Pb-Free Package = Assembly Location

Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

Device	Package	Shipping
MJ21195G	TO-204 (Pb-Free)	100 Units / Tray
MJ21196G	TO-204 (Pb-Free)	100 Units / Tray

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C \pm 5^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Typical	Max	Unit
OFF CHARACTERISTICS		- 1	•			
Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, I _B = 0)			250	-	-	Vdc
Collector Cutoff Current (V _{CE} = 200 Vdc, I _B = 0)		I _{CEO}	-	-	100	μAdc
Emitter Cutoff Current (V _{CE} = 5 Vdc, I _C = 0)	I _{EBO}	-	-	100	μAdc	
Collector Cutoff Current (V _{CE} = 250 Vdc, V _{BE(off)} = 1.5 Vdc)	I _{CEX}	-	-	100	μAdc	
SECOND BREAKDOWN		<u> </u>				
Second Breakdown Collector Current with Base Forward (V _{CE} = 50 Vdc, t = 1 s (non-repetitive) (V _{CE} = 80 Vdc, t = 1 s (non-repetitive)	I _{S/b}	5 2.5	- -	- -	Adc	
ON CHARACTERISTICS		.	1			
DC Current Gain ($I_C = 8$ Adc, $V_{CE} = 5$ Vdc) ($I_C = 16$ Adc, $V_{CE} = 5$ Vdc)		h _{FE}	25 8	- -	75	-
Base-Emitter On Voltage (I _C = 8 Adc, V _{CE} = 5 Vdc)		V _{BE(on)}	-	-	2.2	Vdc
Collector–Emitter Saturation Voltage ($I_C = 8$ Adc, $I_B = 0.8$ Adc) ($I_C = 16$ Adc, $I_B = 3.2$ Adc)	V _{CE(sat)}	- -	- -	1.4 4	Vdc	
DYNAMIC CHARACTERISTICS						
Time Levis Time	h _{FE}	T _{HD}				%
(Matched pair h _{FE} = 50 @ 5 A/5 V)	unmatched h _{FE} matched		_	0.8	-	
Current Gain Bandwidth Product (I _C = 1 Adc, V _{CE} = 10 Vdc, f _{test} = 1 MHz)		f _T	4	-	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	_	-	500	pF	

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%

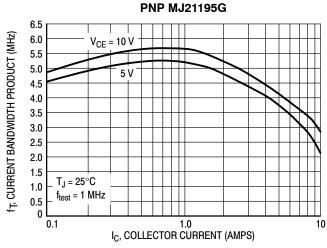


Figure 1. Typical Current Gain Bandwidth Product

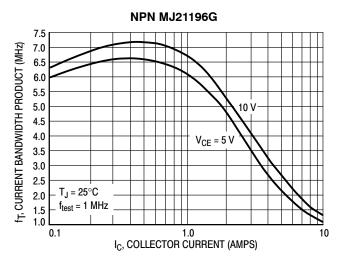


Figure 2. Typical Current Gain Bandwidth Product

TYPICAL CHARACTERISTICS

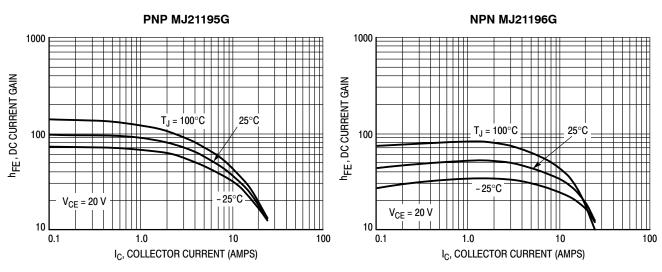


Figure 3. DC Current Gain, V_{CE} = 20 V

Figure 4. DC Current Gain, V_{CE} = 20 V

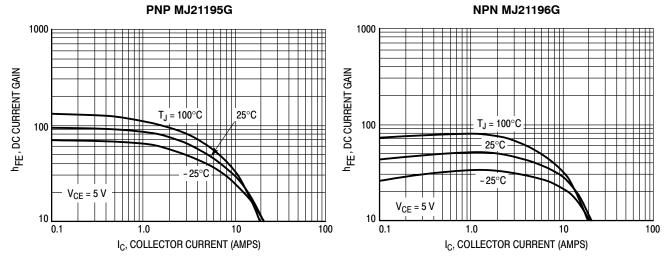


Figure 5. DC Current Gain, V_{CE} = 5 V

PNP MJ21195G NPN MJ21196G 30 30 $I_B = 2 A$ $I_B = 2 A$ 1.5 A 25 25 I_C, COLLECTOR CURRENT (A) 1.5 A I_C, COLLECTOR CURRENT (A) 1 A 1 A 20 20 0.5 A 0.5 A 15 15 10 10 5.0 5.0 $T_J = 25^{\circ}C$ $T_J = 25^{\circ}C$ 0 0 0 25 0 25 V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS) V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 7. Typical Output Characteristics

Figure 8. Typical Output Characteristics

Figure 6. DC Current Gain, V_{CE} = 5 V

TYPICAL CHARACTERISTICS

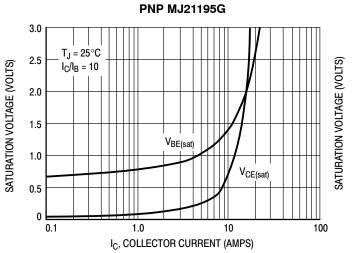


Figure 9. Typical Saturation Voltages

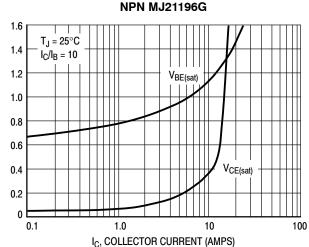


Figure 10. Typical Saturation Voltages

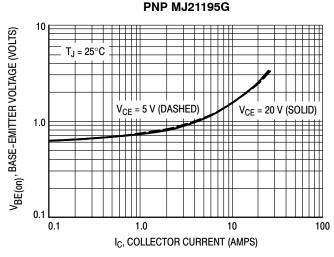


Figure 11. Typical Base-Emitter Voltage

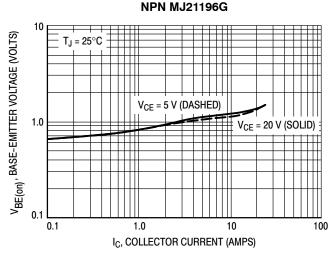


Figure 12. Typical Base-Emitter Voltage

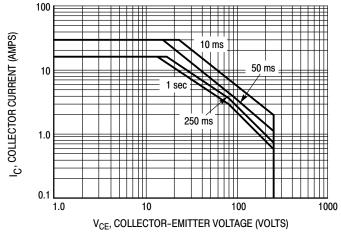


Figure 13. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 13 is based on $T_{J(pk)} = 200^{\circ} C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

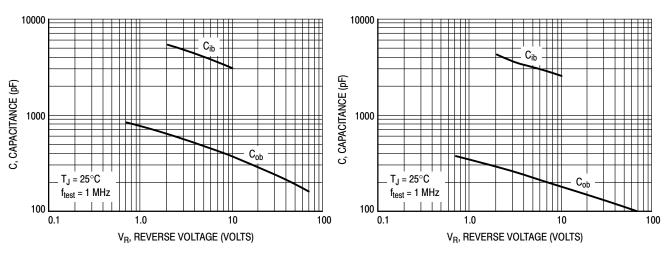


Figure 14. MJ21195 Typical Capacitance

Figure 15. MJ21196 Typical Capacitance

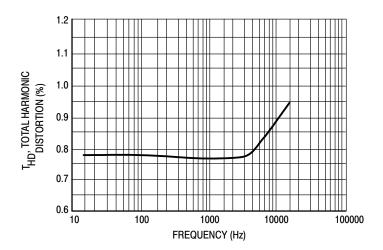


Figure 16. Typical Total Harmonic Distortion

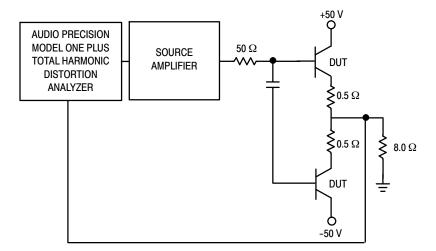
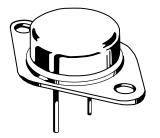


Figure 17. Total Harmonic Distortion Test Circuit

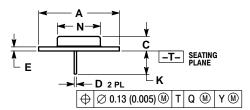


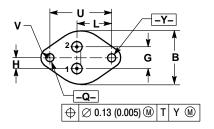


TO-204 (TO-3) CASE 1-07 ISSUE Z

DATE 05/18/1988







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 ALL RULES AND NOTES ASSOCIATED WITH
- 3. ALL HULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37	REF	
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
Е	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46	BSC	
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89	BSC	
N		0.830		21.08	
Ø	0.151	0.165	3.84	4.19	
O	1.187 BSC		30.15	BSC	
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR	STYLE 2: PIN 1. BASE 2. COLLECTOR CASE: EMITTER	STYLE 3: PIN 1. GATE 2. SOURCE CASE: DRAIN	STYLE 4: PIN 1. GROUND 2. INPUT CASE: OUTPUT	STYLE 5: PIN 1. CATHODE 2. EXTERNAL TRIP/DELAY CASE: ANODE
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	
PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE #1	PIN 1. ANODE #1	
2. EMITTER	2. OPEN	2. CATHODE #2	2. ANODE #2	
CASE: COLLECTOR	CASE: CATHODE	CASE: ANODE	CASE: CATHODE	

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